

NOT RECOMMENDED FOR NEW DESIGN **USE DMN2450UFB4**



DMN2400UFB4

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Ultra-Low Package Profile, 0.4mm Maximum Package Height
- ESD Protected up to 1.5kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

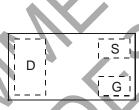
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)



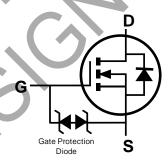




Bottom View



Top View Package Pin Configuration



Equivalent Circuit

Ordering Information (Note 4

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Quantity per Reel
DMN2400UFB4-7	NC	7	8	4	3,000
DMN2400UFB4-7R	NC	7	8	4	3,000
DMN2400UFB4-7B	NC	7	8	2	10,000

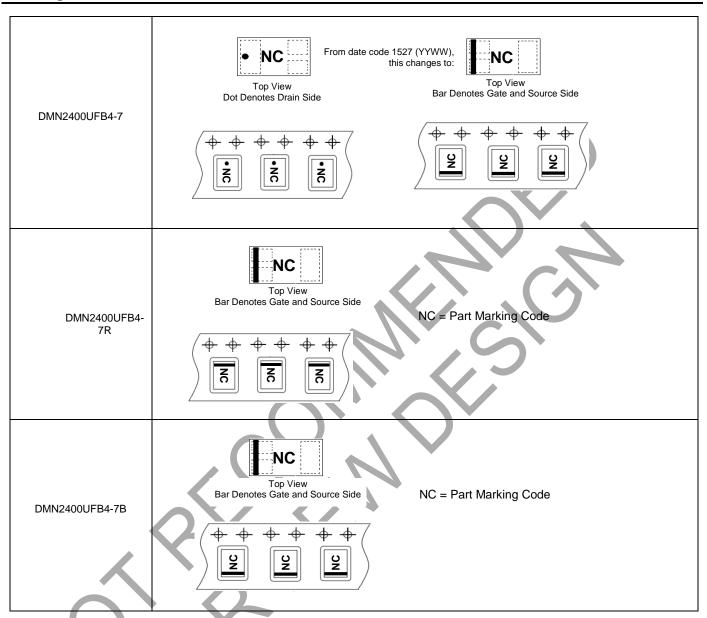
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information





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DMN2400UFB4

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	0.75 0.55	А
Pulsed Drain Current (Notes 5 & 6)		I _{DM}	3	Α	

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	0.47	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	258	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

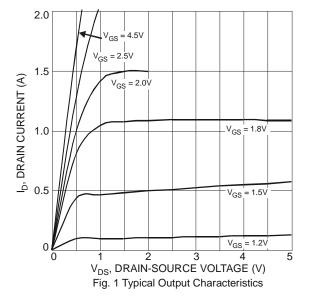
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BV _{DSS}	20	-		V	$V_{GS} = 0V, I_D = 250\mu A$			
Zoro Coto Voltago Drain Current T. 125°C				100	nA	$V_{DS} = 20V, V_{GS} = 0V$			
Zero Gate Voltage Drain Current T _J = +25°C	loss			50	ПА	$V_{DS} = 5V$, $V_{GS} = 0V$			
Gate-Source Leakage	I _{GSS}	1		±100	nA	$V_{GS} = \pm 3V$, $V_{DS} = 0V$			
Gate-Source Leakage	Igss		_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$			
Gate-Source Leakage	lgss		_	±50	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	-	0.9	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			
		_		0.55		$V_{GS} = 4.5V, I_D = 600mA$			
Static Drain-Source On-Resistance	R _{DS} (ON)	_		0.75	Ω	$V_{GS} = 2.5V, I_D = 500mA$			
		_	_	0.9		$V_{GS} = 1.8V, I_D = 350mA$			
Forward Transfer Admittance	Y _{fs}	_	1.0	_	s	$V_{DS} = 10V, I_{D} = 400mA$			
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C _{iss}	_	36.0	_	pF	101/1/			
Output Capacitance	Coss	_	5.7	_	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz			
Reverse Transfer Capacitance	Crss	_	4.2	_	pF	1 = 1.0WH2			
Total Gate Charge	Qg	_	0.5	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$			
Gate-Source Charge	Q _{gs}	_	0.07	_	nC	I _D = 250mA			
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC	1			
Turn-On Delay Time	t _{D(ON)}	_	4.11	_	ns	101/11/			
Turn-On Rise Time	t _R	_	3.82	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$			
Turn-Off Delay Time	t _{D(OFF)}	_	14.8	_	ns	$R_L = 47\Omega, R_g = 10\Omega,$ $I_D = 200 \text{mA}$			
Turn-Off Fall Time	t _F	_	9.6	_	ns	7 ID = 20011IA			

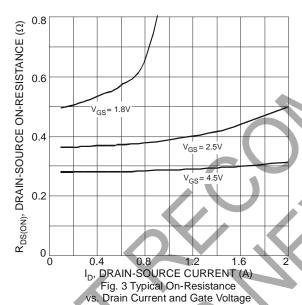
Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

^{6.} Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.







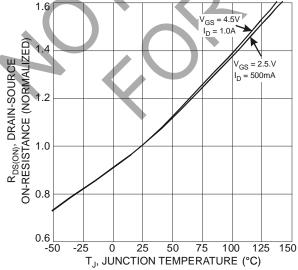
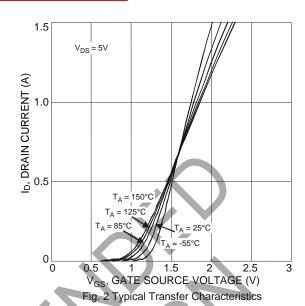


Fig. 5 On-Resistance Variation with Temperature



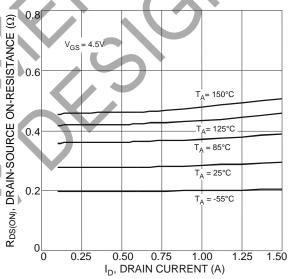


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

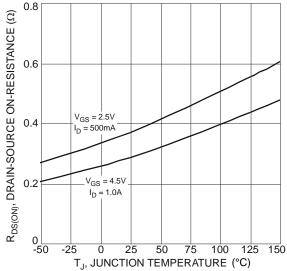


Fig. 6 On-Resistance Variation with Temperature

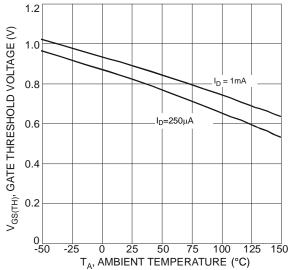
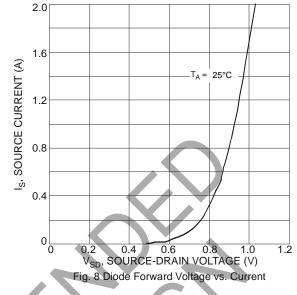
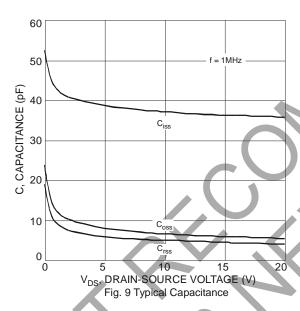


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





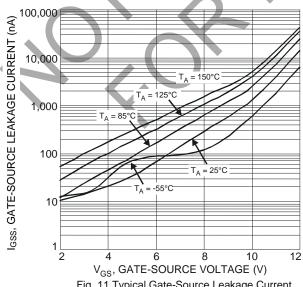
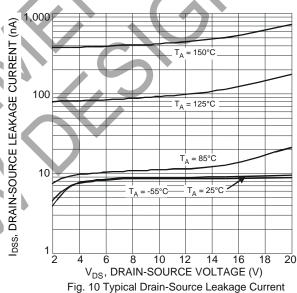


Fig. 11 Typical Gate-Source Leakage Current vs. Gate-Source Voltage



10,000

T_A = 125°C

T_A = 25°C

T_A = 25°C

T_A = 55°C

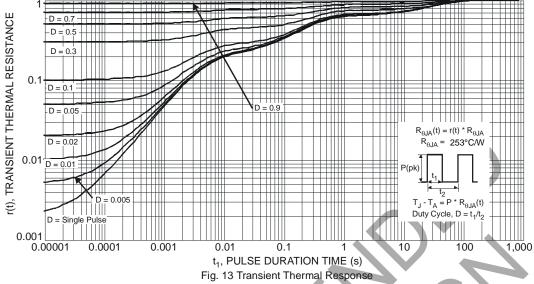
V_{GS} , GATE-SOURCE VOLTAGE (V)

vs. Drain-Source Voltage



DMN2400UFB4



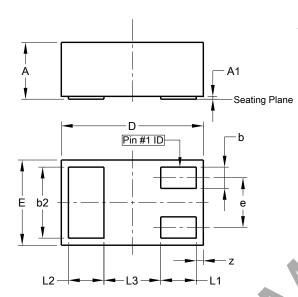




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

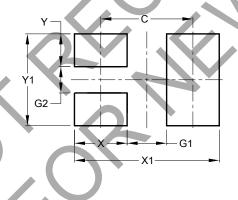


X2-DFN1006-3									
Dim	Min	Max	Тур						
Α	ı	0.40	-						
A 1	0.00	0.05	0.03						
b	0.10	0.20	0.15						
b2	0.45	0.55	0.50						
D	0.95	1.05	1.00						
E	0.55	0.65	0.60						
е	1	ı	0.35						
L1	0.20	0.30	0.25						
L2 0.20 0.30 0.25									
L3	-	1	0.40						
Z	0.02	0.08	0.05						
All Dimensions in mm									

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

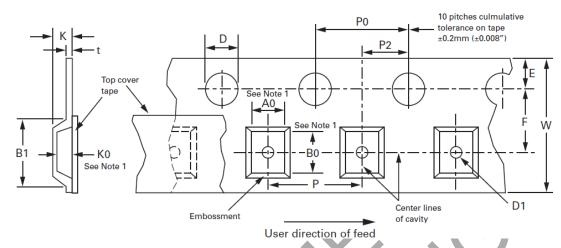


Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



Tape Information

EMBOSSED CARRIER TAPE SPECIFICATIONS



8, 12, 16, 24mm EMBOSSED TAPE DIMENSIONS IN mm								
Tape Size D E P _o tmax A _o B _o K _o								
8mm	1.50 +0.10 -0.0	1.75 ± 0.10	4.0 ± 0.10	0.400	See Note 9	Constant Dimensions		

Tape Size	B1 max	D1 min	F	K max	P2	R min	w	Package Type
8mm	4.5	0.35	3.5 ± 0.05	2.4	2.0 ± 0.05	25	8.0 ± 0.30	Refer to 8mm Device Tape Orientation Table

P									
Tape Size	2.0 ± 0.05	4.0 ± 0.10	8.0 ± 0.10	12.0 ± 0.10	16.0 ± 0.10				
8mm	DFN1006 (-7B)	DFN1006 (-7) DFN1006 (-7R)		_	_				

Note: 9. Ao Bo Ko are determined by component size.



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